





## **Mixed Irradiations: Order Dependent?**

#### Jan-Ole Gosewisch for the ETP Detector Group | November, 2018

Institut für Experimentelle Teilchenphysik (ETP)





#### Introduction



- Strip sensors and diodes irradiated with a total fluence of  $\Phi \approx 6 \times 10^{14} n_{eq} \text{ cm}^{-2}$
- Material (n-type):
  - diffusion oxygenated float zone (DOFZ), magnetic Czochralski (MCZ) and float zone (FZ) – From RD50's NitroStrip project (as in previous talk)
- Irradiation procedure for each material set:
  - 2 sensors and 1 diode irradiated with Φ ≈ 3 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup> protons first and Φ ≈ 3 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup> neutrons afterwards (p+n)
  - 2 sensors and 1 diode irradiated with Φ ≈ 3 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup> neutrons first and Φ ≈ 3 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup> protons afterwards (n+p)
- Measurements:
  - After first irradiation: CV characteristics (-20°C, 455Hz, guard ring floating)
  - After the second irradiation: CV and signal (ALiBaVa with <sup>90</sup>Sr source)
  - Annealing study: Seed signal

## **Irradiation and Annealing**



- Proton irradiation:
  - At ZAG (Karlsruhe) with 23 MeV (hardness factor of 2)
  - Samples are cooled down (to roughly -30°C) while irradiating
  - Measurement of the fluence with a Ni-foil (±15%)
    - → First irradiation with protons  $\Phi = 2.7 \times 10^{14} n_{eq} \text{ cm}^{-2}$
    - → Second irradiation with protons  $\Phi = 2.9 \times 10^{14} n_{eq} \text{ cm}^{-2}$
- Neutron irradiation:
  - At Ljubljana inside a spallation reactor
  - Samples are not cooled inside the reactor (roughly 20h annealing)
  - Real fluences
    - → First irradiation with neutrons  $\Phi = 3 \times 10^{14} n_{eq} \text{ cm}^{-2}$
    - → Second irradiation with neutrons  $\Phi$  = 3.3 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup>
- All equivalent fluence same ( $\Phi = 3 \times 10^{14} n_{eq} \text{ cm}^{-2}$ ) within 10%

## **CV** Characteristics of MCZ Strip Sensors

#### ■ p → p+n

- First  $\Phi = 2.7 \times 10^{14} n_{eq} \text{ cm}^{-2} \text{ protons}$
- Then  $\Phi = 3.3 \times 10^{14} \text{ n}_{eq} \text{ cm}^{-2} \text{ neutrons (p+n)}$ 
  - → Depletion voltage increased (expected)

#### ∎ n <del>→</del> n+p

- First  $\Phi = 3 \times 10^{14} n_{eq} \text{ cm}^{-2}$  neutrons
- Then  $\Phi = 2.9 \times 10^{14} n_{eq} \text{ cm}^{-2} \text{ protons (n+p)}$

→ Depletion voltage unchanged/reduced!





## **CV** Characteristics of FZ Strip Sensors

#### ■ p → p+n

- First  $\Phi = 2.7 \times 10^{14} n_{eq} \text{ cm}^{-2} \text{ protons}$
- Then  $\Phi = 3.3 \times 10^{14} \text{ n}_{eq} \text{ cm}^{-2} \text{ neutrons (p+n)}$ 
  - → Depletion voltage increased (expected)

#### ∎ n <del>→</del> n+p

- First  $\Phi = 3 \times 10^{14} n_{eq} \text{ cm}^{-2}$  neutrons
- Then  $\Phi = 2.9 \times 10^{14} \text{ n}_{eq} \text{ cm}^{-2} \text{ protons (n+p)}$

→ Depletion voltage unchanged/reduced!





## **CV** Characteristics of Diodes



#### ■ p → p+n

- First  $\Phi = 2.7 \times 10^{14} n_{eq} \text{ cm}^{-2} \text{ protons}$
- Then  $\Phi = 3.3 \times 10^{14} \text{ n}_{eq} \text{ cm}^{-2} \text{ neutrons (p+n)}$ 
  - → Depletion voltage increased (expected)

#### ∎ n <del>→</del> n+p

- First  $\Phi = 3 \times 10^{14} n_{eq} \text{ cm}^{-2}$  neutrons
- Then  $\Phi = 2.9 \times 10^{14} n_{eq} \text{ cm}^{-2} \text{ protons (n+p)}$

→ Depletion voltage unchanged/reduced!



## **Short Discussion – Frame Conditions**



#### Result till now:

The irradiation sequence **n+p** leads to a **lower depletion voltage** than **p+n** (all materials)

#### Annealing:

- Irradiation procedure protons + neutrons (p+n)
  - First proton irradiation → sensors are cooled down to -30°C
  - Then shipped to Ljubljana  $\rightarrow$  uncontrolled annealing possible + annealing inside reactor
  - Shipped back  $\rightarrow$  uncontrolled annealing could take place again
- Irradiation procedure for neutrons + protons (n+p)
  - First neutron irradiation (temperature during shipment uncritical)
  - Annealing inside the reactor similar to p+n
  - Shipment back to KIT  $\rightarrow$  same annealing time as for p+n (all sensors in the same package)
  - Irradiation with protons → should be cooled down to -30°C
- Preliminary conclusion: Less depletion voltage (for n+p) due to annealing is only possible if sensors

were not cooled down while irradiating with protons!

## Karlsruher Institut für Technologie

## Signal measurements with an ALiBaVa setup

#### Daughterboard inside a shielded box

- 1 Connection to motherboard
- 2 Beetle chip for readout
- 3 Pitch adapter
- 4 Radioactive source holder
- Copper block temperature controlled via peltier elements (-20°C to 80°C)
- Scintillator below the copper block to trigger the readout
- Measurement procedure
  - Pedestal run to measure the noise
  - Calibration run to calibrate the gain
  - Radioactive source run to measure the generated signal





## Seed Signal vs Cluster Signal



- Charged particle traversing a sensor generates signal in a set of strips (cluster)
  - Seed signal: signal of the strip with the most signal (SNR  $\geq$  4)
  - Cluster signal: seed signal + signal of neighbouring strips (SNR  $\geq$  2)

#### Main difference between cluster and seed signal is an offset

→ Comparison of both signal definitions for a proton irradiated MCZ strip sensor





## **Seed Signal before Annealing**

Voltage dependence of the signal (MCZ)

- Sensors irradiated with n+p show a significantly higher signal for all bias voltages above 300V
- Consistent with the CV characteristics
  - → Lower depletion voltage for n+p



- One sensor with **n+p** clearly above the others
- FZ5 similar signal to p+n for low voltages but higher signal at higher voltages(?)
- Others consistent with CV characteristics
  - $\rightarrow$  Lower depletion voltage for n+p





## **Annealing Characteristics**

- Annealing behaviour at 800V (MCZ)
  - Dependent on the irradiation sequence!
    - $\rightarrow$  Excludes annealing as an explanation for the
    - differences after n+p and p+n irradiation



#### Annealing behaviour at 800V (FZ)

- Independent of the irradiation sequence
- Before annealing: higher signal of n+p
  - $\rightarrow$  Fast vanishing of the difference
- Oxygen concentration
  - MCZ:  $4.6 \cdot 10^{17} \text{ cm}^{-3}$
  - FZ:  $< 9 \cdot 10^{15} \text{ cm}^{-3}$



## Conclusions



- Investigation of CV characteristics and signal dependent on the irradiation sequence
- The irradiation sequence n+p results in a lower depletion voltage than for p+n irradiated samples for all investigated materials (MCZ, FZ, DOFZ)
- In agreement with this lower depletion voltage, the signal is higher (before annealing)
- The signal difference vanishes rapidly (after some days annealing time) due to strong beneficial annealing of the p+n irradiated sensors
  - $\rightarrow$  The signal annealing behaviour is similar for both irradiation sequences and FZ material
- It is ambiguous if this is also the case for DOFZ material
- Contrary, the irradiation sequence was crucial for the annealing behaviour of MCZ material
  - $\rightarrow$  n+p irradiated samples showed significantly less reverse annealing
    - $\rightarrow$  Finally excludes annealing as a possible explanation
- Similar effects were also observed for p-type material
  - $\rightarrow$  But no full comparable data set (CVs of **n**+**p** irradiated sensors)



# Backup

## **Signal Annealing of MCZ Material**





## **Signal Annealing of MCZ Material**





## **HPK Material – CV and IV Characteristics**





## Signal over Fluence of n-type Sensors



From 2017 JINST 12 P06018





#### IV Characteristics n+p vs p+n

After the total fluence of  $\Phi \approx 6e14 \text{ n}_{eq} \text{ cm}^{-2}$ 

- Neutron after proton irradiation (p+n)
  - → More leakage current
- Proton after neutron irradiation (n+p)
  - → Less leakage current







## Signal after Irradiation – FZ and DOFZ 600V



Annealing behaviour of the seed signal (FZ)

- Independent of the irradiation sequence
- Before annealing: higher signal of n+p
  - → Consistent with CV measurements



- Dependent on the irradiation sequence?
- Before annealing: higher signal of n+p
  - → Consistent with CV measurements



## Signal after Irradiation – MCZ 600V



- Annealing behaviour of the seed signal (MCZ) at 600V
  - Still stronger reverse annealing of the **p+n** irradiated material



#### **Voltage Dependence after Annealing**







#### $\rightarrow$ Leakage current increased (expected)

First proton then neutron irradiation (p+n)

Left side:

## **IV Characteristics of DOFZ Material**

Right side:

- First neutron then proton irradiation (n+p)
  - $\rightarrow$  Leakage current unchanged!





## Left side:

- First proton then neutron irradiation (p+n)
  - → Leakage current increased (expected)

## **IV Characteristics of MCZ Material**

#### Right side:

- First neutron then proton irradiation (n+p)
  - → Leakage current unchanged/reduced!





## **IV Characteristics of FZ Material**



#### Left side:

- First proton then neutron irradiation (p+n)
  - → Leakage current increased (expected)

#### Right side:

- First neutron then proton irradiation (n+p)
  - → Leakage current unchanged/reduced!



#### DOFZ8 Protons

## **CV** Characteristics of DOFZ Material

 $p \rightarrow p+n$ 

- First  $\Phi$  = 2.7 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup> protons
- Then  $\Phi = 3.3 \times 10^{14} n_{eq} \text{ cm}^{-2}$  neutrons (p+n)
  - → Depletion voltage increased (expected)

#### $n \rightarrow n+p$

- First  $\Phi = 3 \times 10^{14} n_{eq} \text{ cm}^{-2}$  neutrons
- Then  $\Phi$  = 2.9 x 10<sup>14</sup> n<sub>eq</sub> cm<sup>-2</sup> protons (n+p)

 $\rightarrow$  Depletion voltage unchanged/reduced!



